



	U	1	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20020048862	20020425	10	Fully self-aligned fet technology	438:151	438:163;
			A1					438:305
2	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 20020045320	20020418	11	Nonvolatile memory device and	438:303	365:185.15;
			A1			method for manufacturing the same		438:257
3	<input type="checkbox"/>	<input checked="" type="checkbox"/>	US 200200722325	20020221	12	METHOD OF MAKING ITR A	438:287	438:501



- L26: (35847) 'EEPROM'
- L27: (30041) 26 and memory
- L28: (11389) 27 and flash
- L29: (1919) 28 and (implantation implanting implant\$2)
- L30: (1519) 29 and (mask\$3 resist photo-resist phot adj resist resist)
- L31: (1440) lightly adj3 source
- L32: (77) 30 and 31
- L33: (77) 32 and (source drain s/d source/drain drain)
- L34: (62) 33 and (channel adj region)
- L35: (57) 34 and (control adj gate floating adj gate)
- L36: (283) ((lightly adj3 source) with (mask\$3 resist photo adj resist ph
- L37: (8) 36 and 'EEPROM'
- L38: (100) 31 and 26
- L39: (73) 38 and 29
- L40: (96) 38 and (implantation implanting implant\$2)
- L41: (95) 40 and (mask\$3 resist photo-resist phot adj resist resist)
- L42: (95) 41 and (source drain s/d source/drain drain)

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DBs USPAT; US-PGPUB; EPO; JPO; DEF  Plurals

Default operator:  OR

Highlight all hit terms initially

41 and (source drain s/d source/drain drain)

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	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef
1	<input type="checkbox"/>	<input type="checkbox"/>	US 6359305 B1	20020319	21	Trench-isolated EEPROM flash in segmented bit line page architecture	257/316	257/321;
2	<input type="checkbox"/>	<input type="checkbox"/>	US 6356486 B1	20020312	40	Electrically alterable non-volatile memory with n-bits per cell	365/189.01	438/267;
3	<input type="checkbox"/>	<input type="checkbox"/>	US 6353554 B1	20020305	57	Memory apparatus including	365/185.03	365/185.2;

Hits  Details  HTML



- L26: (35847) 'EEPROM'
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- L32: (77) 30 and 31
- L33: (77) 32 and (source drain s/d source/drain drain)
- L34: (62) 33 and (channel adj region)
- L35: (57) 34 and (control adj gate floating adj gate)
- Failed

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34 and (control adj gate floating adj gate)

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	U	I	Document ID	Issue Date	Pages	Title	Current OR	Current XRef	▲
1	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6359305 B1	20020319	21	Trench-isolated EEPROM flash in segmented bit line page architecture	257/316	257/321;	
2	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6356486 B1	20020312		Electrically alterable non-volatile memory with n-bits per cell	365/189.01	438/267;	
3	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6353554 B1	20020305		Memory apparatus including programmable non-volatile multi-bit	365/185.03	365/185.1;	
4	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6344998 B1	20020205		Electrically alterable non-volatile memory with N-Bits per cell	365/185.2;	365/189.01,	
5	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6343034 B1	20020129		Electrically alterable non-volatile memory with n-bits per cell	365/189.01	365/230.01,	
6	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6339545 B1	20020115		Electrically alterable non-volatile memory with n-bits per cell	365/185.03	365/230.02	
7	<input checked="" type="checkbox"/>	<input type="checkbox"/>	US 6335549 B1	20020101		EEPROM with high channel hot carrier injection efficiency	257/231	365/201;	
								365/207;	
								257/315;	
								257/221;	

Hits  Details  HTML



- Drafts
- Pending
- Active

- L1: (7326) (memory same flash) and 'EEPROM'
- L2: (1691) 1 and (implantation implanting implant\$2)
- L3: (1662) 2 and (source drain s/d source/drain)
- L4: (1348) 3 and mask\$3
- L5: (1335) 4 and gate
- L6: (107) 5 and (lightly near3 source)
- L7: (966) 5 and (channel near3 region)
- L8: (91) 7 and (lightly near3 source)

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DBs USPAT; US\_PGPUB; EPO; JPO; DERWENT; IBM\_TDB  Plurals

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Type	Hits	Search Text	DBs	Time Stamp	Comments

Hits  Details  HTML

Ready

NUM

 Pending Active

- L1: (7326) (memory same flash) and 'EEPROM'
- L2: (1691) 1 and (implantation implanting implant\$2)
- L3: (1662) 2 and (source drain s/d source/drain)
- L4: (1348) 3 and mask\$3
- L5: (1335) 4 and gate
- L6: (107) 5 and (lightly near3 source)
- L7: (966) 5 and (channel near3 region)
- L8: (91) 7 and (lightly near3 source)
- L17: (21019) 'EEPROM'
- L18: (37762) 'EEPROM'
- L19: (10777) (memory same flash) and 'EEPROM'
- L21: (7392) 19 and (source s/d drain source/drain)
- L24: (4059) 21 and (control adj gate floating adj gate)
- L25: (1835) 24 and (mask\$3 resist photo and resist resist)

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24 and (mask\$3 resist photo and resist resist)

    

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